

L Number	Hits	Search Text	DB	Time stamp
-	3203	438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/12 10:56
-	18	(438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:46
-	1	(sixth adj mask\$3) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:21
-	70	(438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with well) and (low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 18:40
-	68	((438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with well) and (low with voltage with well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:47
-	324	(high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:55
-	39	((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with (p adj (body or region or well)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
-	0	20030162375.URPN.	USPAT	2003/12/15 18:43
-	44	257/548.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:13
-	35	((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with p with high with voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
-	7	((first with mask\$3) same (implant\$5 with high with voltage with well)) and ((second with mask\$3) same (first with low with voltage with well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:57
-	2579	high with voltage with well with (implant\$5 or form\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:22
-	201	low with voltage with well with (implant\$5 or form\$3) with first	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
-	196	low with voltage with well with (implant\$5 or form\$3) with second	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
-	114	(high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
-	3208	438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:24

-	11	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:52
-	6	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:42
-	7	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
-	8	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with mask\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
-	144	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
-	131	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
-	1	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with photoresist with film)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:53
-	1	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:55
-	5	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:58
-	21	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:59
-	1	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and photodiode and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:04
-	3	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:10
-	21	(high with voltage with well) and (low with voltage with well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:35
-	1	(high adj voltage adj well) and (low adj voltage adj well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:11

-	2	cmos same dmos same mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:04
-	10	cmos and dmos and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:05
-	2420	mem same (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	2420	mems same (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	1862	mems with (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	509	mems with accelerometer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	2	cmos same dmos same photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:18
-	16	cmos and dmos and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:05
-	31	cmos same dmos same soi	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:18
-	2	5578506.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:30
-	2	5681761.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:30
-	113	(high with voltage with well) and (low with voltage with well) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:36
-	104	((high with voltage with well) and (low with voltage with well) and photodiode) and @ad<20020222	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:47
-	1	(high adj voltage adj well) and (low adj voltage adj well) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:37
-	71986	photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:48
-	67	photodiode and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:48
-	35	(implant\$5 with high with voltage with well) and (implant\$5 with low with voltage with well) and (first adj mask) and (second adj mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:03

-	28	((implant\$5 with high with voltage with well) and (implant\$5 with low with voltage with well) and (first adj mask) and (second adj mask) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:21
-	0	((implant\$5 with high with voltage with well) same (first adj protective)) and ((implant\$5 with low with voltage with well) same(second adj protective)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:23
-	0	((implant\$5 with high with voltage with well) same (first adj oxide)) and ((implant\$5 with low with voltage with well) same(second adj oxide)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:23
-	0	((implant\$5 with high with voltage with well) same (first with protective)) and ((implant\$5 with low with voltage with well) same(second with protective)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 15:48
-	8	((implant\$5 with high with voltage with well) same (first with oxide)) and ((implant\$5 with low with voltage with well) same(second with oxide)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:41
-	152	((implant\$5 with high with voltage with well) same (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:28
-	77	((implant\$5 with high with voltage with well) same (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222)) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:28
-	7	(implant\$5 with high with voltage with well with first with mask) and (implant\$5 with low with voltage with well with second with mask) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:42
-	3	((high with voltage with well) same (first with protective)) and ((low with voltage with well) same (second with protective)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 15:50
-	18	((high with voltage with well) same (first with mask)) and ((low with voltage with well) same (second with mask)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 16:46
-	30	((high with voltage with well) same (first with oxide)) and ((low with voltage with well) same (second with oxide)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 17:38
-	54	((high with voltage with implant\$5) same (first with mask)) and ((low with voltage with implant\$5) same (second with mask)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 16:46
-	0	(implant\$5 with high with voltage with well) and ((low with voltage with well) same (remov\$3 with second with portion with first with mask)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 17:40
-	44	(high with voltage with well) and (low with voltage with well) and (remov\$3 with second with portion with first with mask) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:16
-	867	(438/200.ccls. or 438/279.ccls.) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:17

-	205	((438/200.ccls. or 438/279.ccls.) and (@ad<20020222 or @rlad<20020222)) and (high with voltage) and (low with voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:17
-	159	((438/200.ccls. or 438/279.ccls.) and (@ad<20020222 or @rlad<20020222)) and (high with voltage) and (low with voltage)) and mask\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:18
-	0	wo200237547	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/12 10:56
-	1	"wo 200237547"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/12 10:58
-	4	985447.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/12 10:58